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## **Spatially confined magnesiothermic reduction induced uniform mesoporous hollow silicon carbide nanospheres for high-performance supercapacitors**

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### **Experimental section**

#### **Materials.**

1-Ethyl-3-methylimidazolium tetrafluoroborate (EMIMBF<sub>4</sub> > 99%), KOH and HCl are analytical quality and purchased from Jiangsu Guotai Super Power New Materials Co., Ltd. Formaldehyde, magnesium powder, CTAB (hexadecyl trimethyl ammonium bromide) and 3-aminophenol were bought from Sinopharm Chemical Reagent Co., Ltd.

#### **Synthesis of mesoporous hollow carbon/silica spheres (MHS-SiO<sub>2</sub>/C).**

During the synthesis of (MHS-SiO<sub>2</sub>/C), CTAB (0.55 g) and resorcinol (0.21 g) were suspended in a solution with 9 ml ethanol and 23 ml deionized water at 25 °C. After resorcinol absolutely dissolved, ammonia solution (NH<sub>4</sub>OH, 0.22 mL, ~25wt. %) was inserted and stirred for 10 min. Then add 0.29 mL of formaldehyde, let stand for a few minutes until it turned transparent and becomes an emulsion. After that, 1 ml of TEOS was added immediately, and the prepared solution was stirred at 25 °C for 24 h, then heated in Teflon lined autoclave at 80 °C for another 24 hours. The solid product was produced by centrifugation and freeze drying. MHSs-C/SiO<sub>2</sub> composites were obtained by annealing the solid product at 800 °C for 2.5 h with a ramp rate of 1.5 °C min<sup>-1</sup> in N<sub>2</sub> atmosphere. Furthermore, excess silica was eliminated by 10% HF solution for 24 h, thus mesoporous hollow carbon spheres (MHS-C) were produced. The MHS-C/SiO<sub>2</sub> composites were calcined at 600 °C for 6 h in air to produce the mesoporous hollow silica spheres.

## Magnesiothermic reduction (MR) technology prepares mesoporous hollow SiC nanospheres (MHS-SiC).

MHS-SiC material was synthesized by the interfacial interaction of SiO<sub>2</sub> and carbon during MR process. A specific quantity of MHS-SiO<sub>2</sub>/C and pure magnesium powders were mixed and placed into a ceramic, which was subsequently transferred to a tube furnace in argon atmosphere. With a ramp of 5 °C min<sup>-1</sup>, the furnace was heated to 620 °C and maintained for 3.0 h. The acquired sample was then collected after returning to room temperature in a pure argon atmosphere. To get eliminate the by-product MgO from the sample, pure water and 1.0 M HCl solution were utilized. The 5 wt% HF solution was used to eliminate the unreacted SiO<sub>2</sub>. The resulting sample was subsequently purified, cleaned with deionized water, and dried under vacuum at 110 °C. This as-prepared product is known as MHS-SiC.

### Characterization.

Field emission scanning electron microscopy (FESEM) and Transmission electron microscopy (TEM) examinations were carried out using the Hitachi S-4800, Tecnai G2 F30 S-Twin. PANalytical-X-pert diffractometer (Cu K radiation at 40mA and 40kV) was used to detect powder X-ray diffraction (XRD) patterns (10-80° in 2θ). On a Malvern Zetasizer NanoZS instrument, dynamic light scattering (DLS) parameters were determined. For the XPS examination, an Axis Ultra spectrometer was employed. Micromeritics-ASAP-2020 was used to measure the nitrogen adsorption-desorption isotherm at 77K and relative pressure  $p/p_0$  of  $1.2 \times 10^{-6}$ -0.990. Test samples were degassed at 250 °C for at least 4 hours before to the measurement. Pore size distribution and specific surface area ( $S_{\text{BET}}$ ) were determined by density functional theory (DFT) calculations and Brunauer-Emmett-Teller (BET) measurements.

### Electrochemical measurements.

The electrochemical characteristics of MHS-SiC were investigated in both EMIMBF<sub>4</sub> and 6 M KOH electrolytes. The electrodes were prepared by mixing MHS-SiC (86 wt. %), PTFE binder (4 wt. %) and acetylene black (10 wt. %). The EDLC current collectors were stainless steel (6 M KOH electrolyte) and aluminium mesh (EMIMBF<sub>4</sub> electrolyte) with 5-7 mg/ cm<sup>2</sup> electrode materials. Subsequently, the electrodes were vacuum-dried at 110°C for 8 hours. And polypropylene membrane was selected as separator. The cyclic voltammetry (CV), galvanostatic charge/discharge, and AC impedance spectroscopy (EIS) were measured through the CHI660E electrochemical workstation. With a 5 mV voltage amplitude, impedance spectra were measured in frequency range of 0.01 Hz–10 kHz. The capacitor's cutoff charge voltage of 6 M KOH solution was set to 0-1.0 V, while the cutoff charge voltage of EMIMBF<sub>4</sub> solution was 0-3.5 V.

Equation (1) was used to determine the specific capacitance for a single electrode.

$$c_g = \frac{2I}{(dV/dt)m} \quad (1)$$

Where  $dV/dt$ (V/s) = slope of a discharge curve,  $m$ (g) = single electrode active material mass, and  $I$ (A) = discharge current.  $P_{\text{cell}}$  (specific power density) and  $E_{\text{cell}}$  (specific energy density) calculations were also evaluated for symmetrical supercapacitors, which are mentioned in the equation (2) and (3).

$$P_{\text{cell}} = \frac{E_{\text{cell}}}{t} \quad (2)$$

$$E_{cell} = \frac{C_g \Delta V^2}{8 \times 3.6} \quad (3)$$

Here,  $t(h)$ , and  $\Delta V(V)$  represented the discharge time and cell voltage after ohmic drop, respectively.

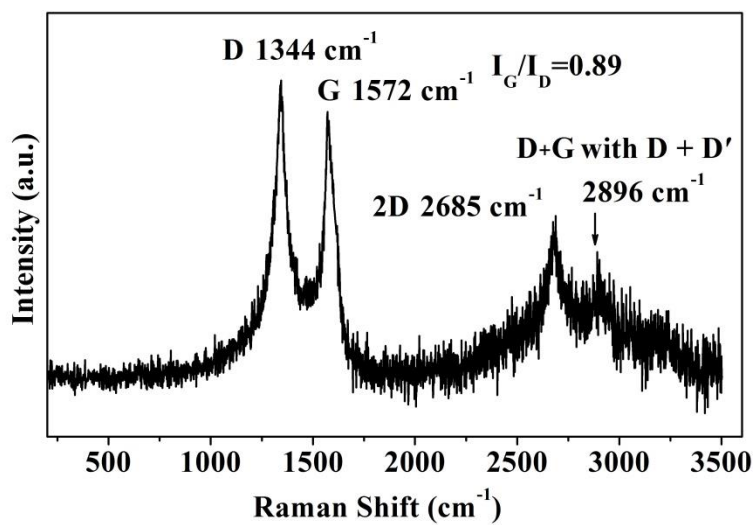


Fig. S1. Raman spectrum of MHS-SiC.

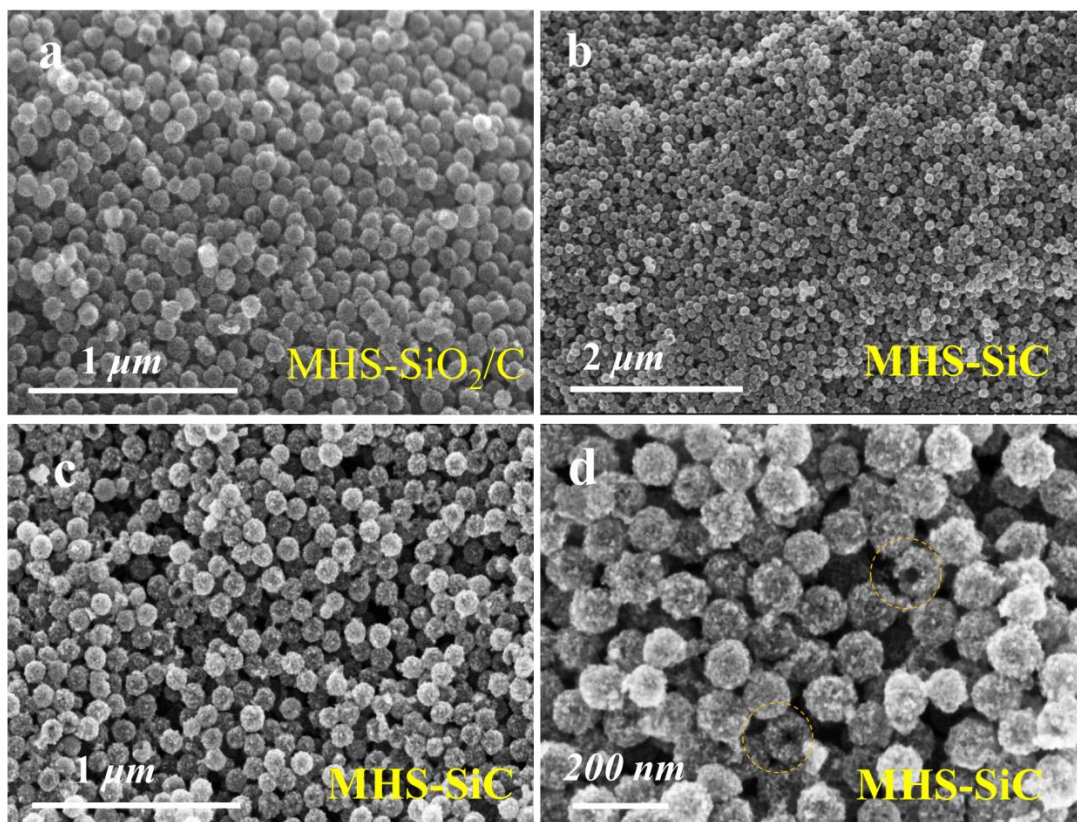


Fig. S2. (a) SEM images of MHS-SiO<sub>2</sub>/C, (b, c,d) SEM images of MHS-SiC, the marked circles show the hollow structures.



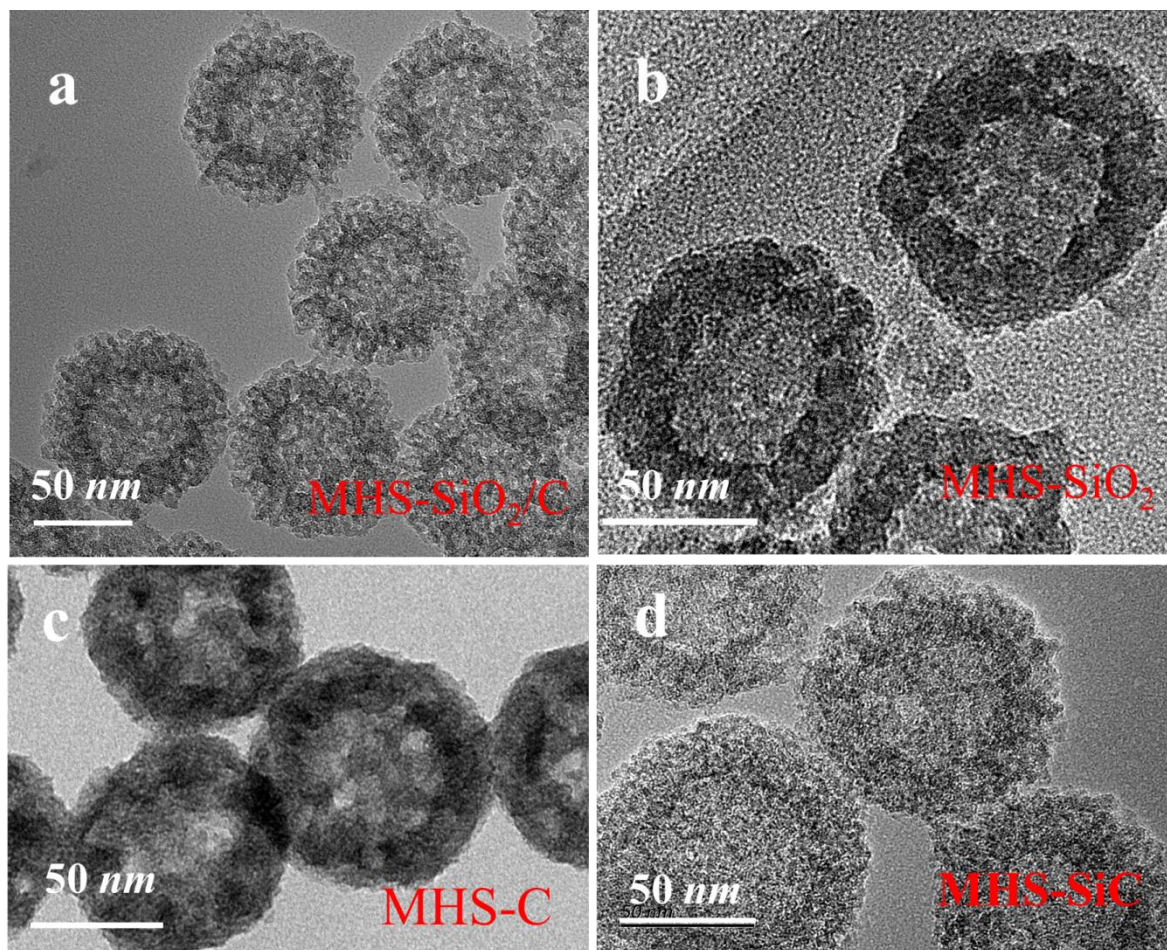


Fig. S3. TEM images of (a) MHS-SiO<sub>2</sub>/C, (b) MHS-SiO<sub>2</sub>, (c) MHS-C and (d) MHS-SiC.

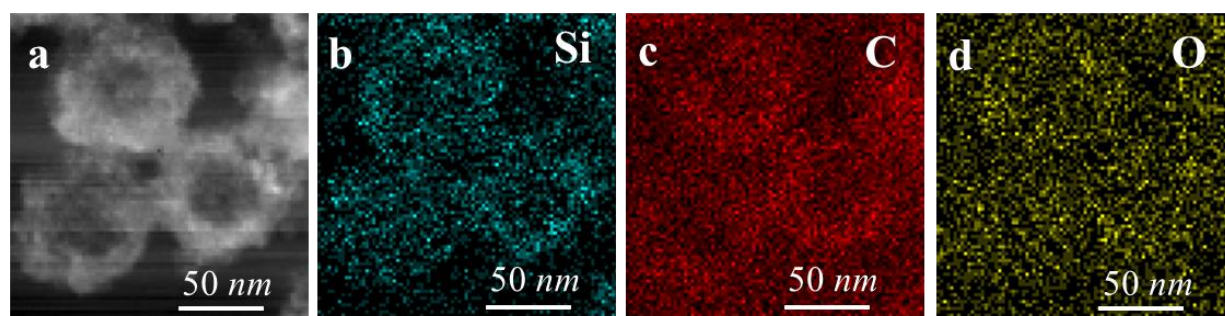


Fig. S4. (a) STEM, and corresponding (b-d) elemental mapping images of MHS-SiC

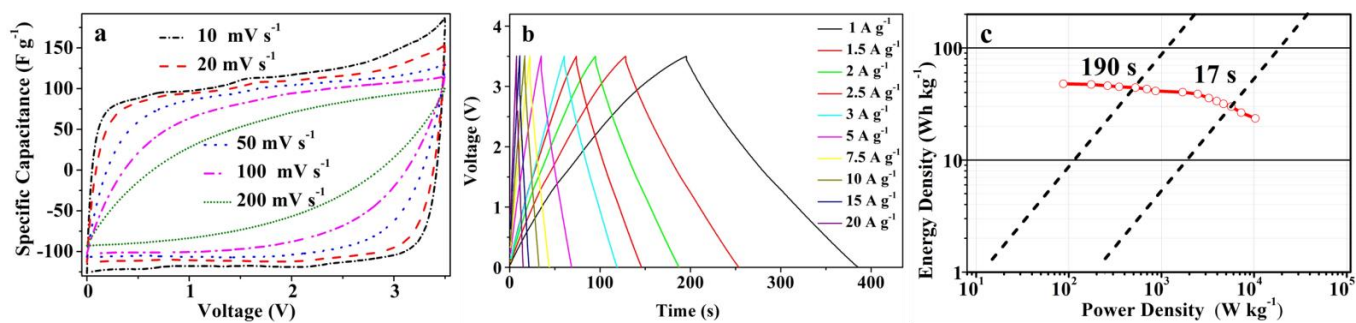


Fig. S5. (a) Cyclic voltammograms, (b) Galvanic charge-discharge curves, (c) Ragone plot of MHS-SiC in ionic liquid EMIMBF<sub>4</sub> electrolyte.

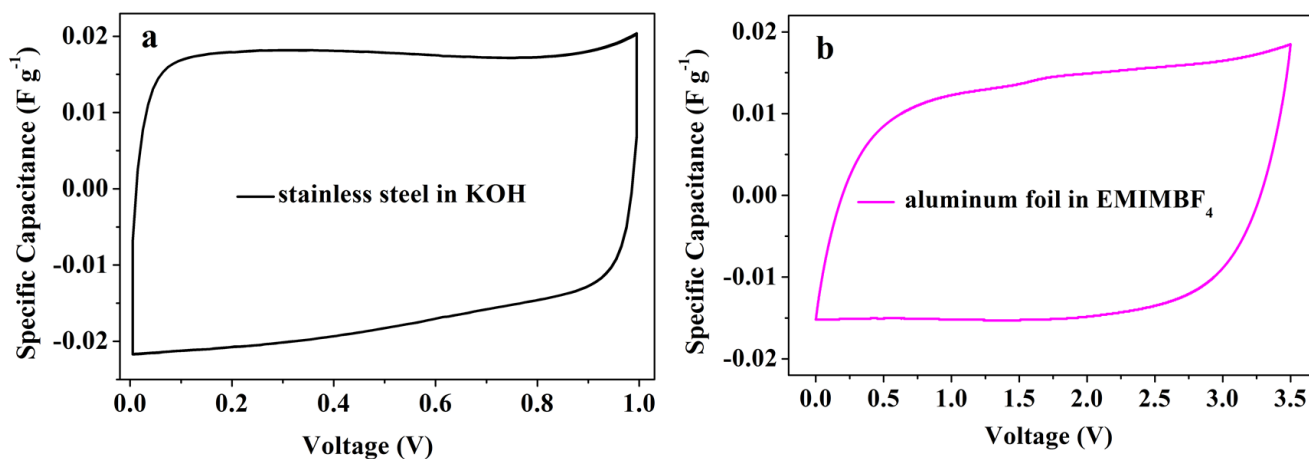


Fig. S6. (a) Cyclic voltammograms of stainless steel in KOH and aluminum foil in EMIMBF<sub>4</sub> electrolyte at a scan rate of 0.1 V s<sup>-1</sup>.

**Table S1.** Comparison of specific surface area, pore volume and specific capacitance of the obtained **MHS-SiC** sample with previously reported samples.(a is a two-electrode system, and b is a three-electrode system)

Materials	$S_{\text{BET}}$ ( $\text{m}^2 \text{g}^{-1}$ )	Pore volume ( $\text{cm}^3 \text{g}^{-1}$ )	Capacitance ( $\text{F g}^{-1}$ )	Current density	Electrolyte	Ref.
<b>Mesoporous Hollow SiC Nanospheres (MHS-SiC)</b>	<b>868</b>	<b>1.49</b>	<b>134</b>	<b>0.1 A g<sup>-1</sup></b>	<b>6 M KOH</b>	<b>This work<sup>a</sup></b>
			<b>116</b>	<b>100 A g<sup>-1</sup></b>		
			<b>114</b>	<b>0.1 A g<sup>-1</sup></b>	<b>EMIMBF<sub>4</sub></b>	
			<b>86</b>	<b>20 A g<sup>-1</sup></b>		
silicon-oxy-carbide (SiOC)	5.64		102.3	5 mA g <sup>-1</sup>	1 M Li <sub>2</sub> SO <sub>4</sub> 1 M TEABF <sub>4</sub>	1 <sup>a</sup>
SiC nanowires	-	-	29.5	0.25 A g <sup>-1</sup>	2 M KCl	2 <sup>b</sup>
Silicon Carbide Nanocauliflowers	-	-	72	1.43 A g <sup>-1</sup>	1 M Na <sub>2</sub> SO <sub>4</sub>	3 <sup>a</sup>
			41	0.71 A g <sup>-1</sup>		
ordered mesoporous SiC@C	757.4	-	194.8	0.2 A g <sup>-1</sup>	6 M KOH	4 <sup>b</sup>
			123	5 A g <sup>-1</sup>		
SiC/C nanosheets			130	10 mV s <sup>-1</sup>	1 M Na <sub>2</sub> SO <sub>4</sub>	5 <sup>b</sup>
			69	0.5V s <sup>-1</sup>		
SiC nanowire-derived carbon	1182	-	200	2 A g <sup>-1</sup>	6 M KOH	6 <sup>a</sup>
			95	10 A g <sup>-1</sup>		
porous carbon/ silicon carbide	1357.9	0.76	234.2	1 A g <sup>-1</sup>	1 M Na <sub>2</sub> SO <sub>4</sub>	7 <sup>b</sup>
			167.3	20 A g <sup>-1</sup>		
boron-doped SiC thin film on silicon		-	232	2.2 A g <sup>-1</sup>	1 M H <sub>2</sub> SO <sub>4</sub>	8 <sup>b</sup>
			198	2 mV s <sup>-1</sup>		
			116	80 mV s <sup>-1</sup>		
SiCNWs@ NiCo <sub>2</sub> O <sub>4</sub> NCs	55.4		131	1 A g <sup>-1</sup>	PVA-KOH	9 <sup>a</sup>
			72	20 A g <sup>-1</sup>		
C doped SiC	1789		162	0.5 A g <sup>-1</sup>	PVA-H <sub>2</sub> SO <sub>4</sub>	10 <sup>a</sup>
			102	10 A g <sup>-1</sup>		

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